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Kind regards,

Team Nexperia

# PEMB19; PUMB19

## PNP/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

Rev. 02 — 1 September 2009

**Product data sheet** 

## 1. Product profile

## 1.1 General description

PNP/PNP resistor-equipped transistors

Table 1. Product overview

Type number			NPN/PNP	NPN/NPN	
	NXP	JEITA	complement	complement	
PEMB19	SOT666	-	PEMD19	PEMH19	
PUMB19	SOT363	SC-88	PUMD19	PUMH19	

### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

## 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-50	V
I <sub>O</sub>	output current (DC)		-	-	-100	mA
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ



PNP/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

#### **Pinning information** 2.

Table 3. **Pinning** 

14510 0.	· · · · · · · · · · · · · · · · · · ·		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		TR2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R1   R1
			1 2 3 006aaa268

#### **Ordering information** 3.

Table 4. **Ordering information** 

Type number	Package	Package					
	Name	Description	Version				
PEMB19	-	plastic surface mounted package; 6 leads	SOT666				
PUMB19	SC-88	plastic surface mounted package; 6 leads	SOT363				

## **Marking**

**Product data sheet** 

Table 5. **Marking codes** 

Type number	Marking code <sup>[1]</sup>
PEMB19	6D
PUMB19	T3*

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

PNP/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

## 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
$V_{CBO}$	collector-base voltage	open emitter	-	-50	V
$V_{CEO}$	collector-emitter voltage	open base	-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-5	V
Io	output current (DC)		-	-100	mA
I <sub>CM</sub>	peak collector current		-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	SOT363		<u>[1]</u> -	200	mW
	SOT666		[1] [2] -	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
Per device					
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1] [2] _	300	mW

<sup>[1]</sup> Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

## 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25  ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		[1] [2]	-	625	K/W
Per device						
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		[1] [2]	-	416	K/W

<sup>[1]</sup> Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

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<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

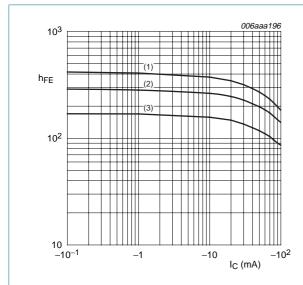
<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

## **Characteristics**

Table 8. **Characteristics** 

T<sub>amb</sub> = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I <sub>CEO</sub>	collector-emitter	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	-1	μΑ
cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	-50	μΑ	
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ mA}$	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-150	mV
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF



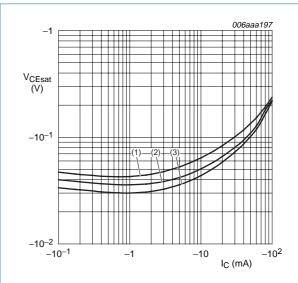


- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$

**Product data sheet** 

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

DC current gain as a function of collector Fig 1. current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ 

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values

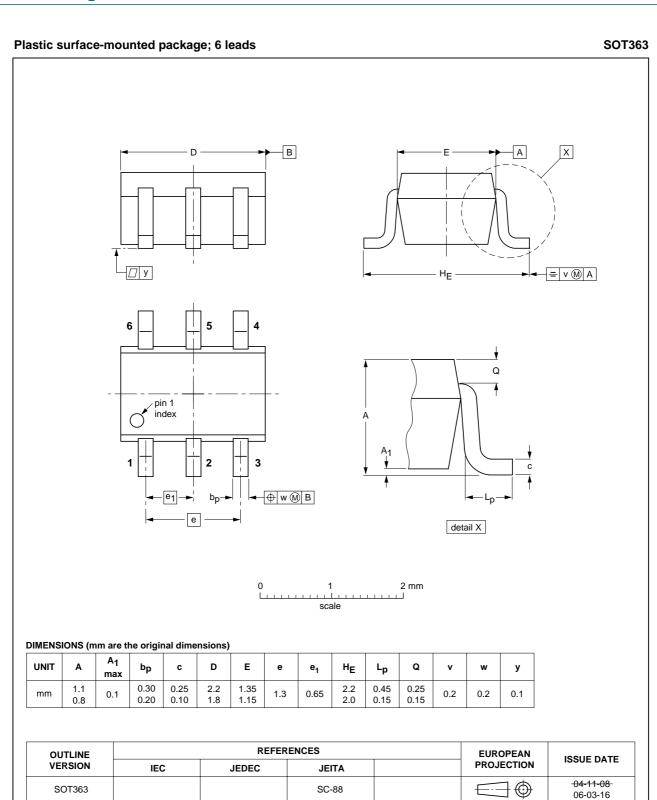
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#### **Package outline** 8.



Package outline SOT363 (SC-88) Fig 3.

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PNP/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

## **SOT666** Plastic surface-mounted package; 6 leads - A Х ΗE pin 1 index С ⊕ w M A detail X 2 mm scale **DIMENSIONS** (mm are the original dimensions) UNIT Ε D Α bp e<sub>1</sub> $H_{\mathsf{E}}$ $L_{p}$ у 0.6 0.27 0.18 1.7 1.3 1.7 0.3 0.5 0.5 0.17 0.08 1.5 0.1 1.1 REFERENCES **EUROPEAN** OUTLINE ISSUE DATE VERSION **PROJECTION** IEC **JEDEC** JEITA 04-11-08 $\bigcirc$ SOT666 06-03-16

Fig 4. Package outline SOT666

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PNP/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

## **Packing information**

Table 9. **Packing methods** 

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description		Packing qua	ntity	
				3000	4000	10000
PEMB19	SOT666	4 mm pitch, 8 mm tape and reel;		-	-115	-
PUMB19	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-135
PUMB19	SOT363	4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-165

[1] For further information and the availability of packing methods, see Section 12.

[2] T1: normal taping

[3] T2: reverse taping

**Product data sheet** 

# PEMB19; PUMB19

PNP/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

## 10. Revision history

## Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMB19_PUMB19_2	20090901	Product data sheet	-	PEMB19_PUMB19_1
Modifications:		eet was changed to reflect v legal definitions and disc		
	<ul><li>Figure 3 "Pac</li></ul>	ckage outline SOT363 (SC	-88)": updated	
	<ul><li>Figure 4 "Pac</li></ul>	ckage outline SOT666": up	dated	
PEMB19_PUMB19_1	20050202	Product data sheet	-	-

PNP/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

## 11. Legal information

#### 11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- The term 'short data sheet' is explained in section "Definitions
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PNP/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

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